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Inclosure Material:	
Metal all transistor	
Overall Length:	
1.573 inches 2nd transist	tor
Overall Height:	
0.340 inches 1st transiste	r
Overall Width:	
1.050 inches 2nd transist	tor
End Application:	
F-16 a/b aircraft	
Mounting Facility Quant	tity:
2 all transistor	
Internal Configuration:	
Junction contact all transi	stor
Electrode Internally-elec	ctrically Connected To Case:
Collector all transistor	
Internal Junction Config	juration:
Pnp 1st transistor	
Component Function Re	elationship:
Matched	
Component Name And	Quantity:
2 transistor	
Mounting Method:	
Unthreaded hole all trans	istor
Semiconductor Material	:
Silicon all transistor	
Voltage Rating In Volts	Per Characteristic:
275.0 collector to base v	oltage/static/emitter open 1st transistor and 225.0 collector to emitter voltage/static/base open 1st transistor and
6.0 emitter to base volta	ge, static, collector open 1st transistor
Current Rating Per Char	racteristic:
20.00 amperes source cu	toff current 2nd transistor and 50.00 amperes source cutoff current 2nd transistor
Power Rating Per Chara	icteristic:
250.0 watts small-signal i	nput power, common-collector preset 2nd transistor
Maximum Operating Te	mpurature Per Measurement Point:
200.0 degrees celsius am	ibient air 1st transistor
Terminal Type And Qua	ntity:
2 pin all transistor and 1 c	case all transistor
Shelf Life:	
N/a	
Unit Of Measure:	
Demilitarization:	

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